

# N-channel SiC power MOSFET

V <sub>DSS</sub>	1200V
R <sub>DS(on)</sub> (Typ.)	18mΩ
I <sub>D</sub> *1	75A
$P_D$	267W

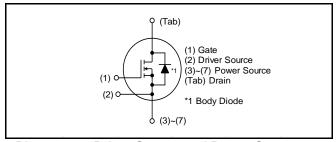
### Outline



### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

#### Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

### Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

### Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4018KW7

### ● **Absolute maximum ratings** (T<sub>vi</sub> = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		$V_{DSS}$	1200	V	
Continuous drain	\/ -\/	$T_c = 25^{\circ}C$	I <sub>D</sub> , I <sub>S</sub> *1	75	А
and source current	$V_{GS} = V_{GS\_on}$	$T_c = 100$ °C	I <sub>D</sub> , I <sub>S</sub>	53	Α
Pulsed drain current	$V_{GS} = V_{GS\_on}$	$T_c = 25^{\circ}C$	I <sub>D,pulse</sub> *2	179	Α
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I <sub>S,pulse</sub> *1,*3	75	Α
Body diode surge forward current		V <sub>GS</sub> = 0 V	179	Α	
Gate - source voltage (DC)		$V_{GSS\_DC}$	-4 to +21	V	
Gate - source surge voltage (t <sub>surge</sub> < 300ns)		V <sub>GSS_surge</sub> *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		$V_{GS\_on}^{*6}$	+15 to +18	V	
Recommended turn-off gate - source drive voltage		$V_{GS\_off}$	0	V	
Virtual junction temperature		$T_{vj}$	175	°C	
Range of storage temperature		$T_{stg}$	-40 to +175	°C	

# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

Parameter	Symbol Conditions -	Values			Unit	
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown	W	$V_{GS} = 0 \text{ V}, I_D = 18.6\text{mA}$				V
voltage	V (BR)DSS	$T_{vj} = 25^{\circ}C$	1200	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 1200 \text{V}$				
Zero Gate voltage Drain current	I <sub>DSS</sub>	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T <sub>vj</sub> = 150°C	-	10	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +21V$ , $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	000	$V_{GS} = -4V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_D = 22.2mA$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 42A$				_
Static Drain - Source on - state resistance	R <sub>DS(on)</sub> *8	$T_{vj} = 25^{\circ}C$	-	18.0	23.4	mΩ
		T <sub>vj</sub> = 150°C	-	36.0	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	1	-	Ω

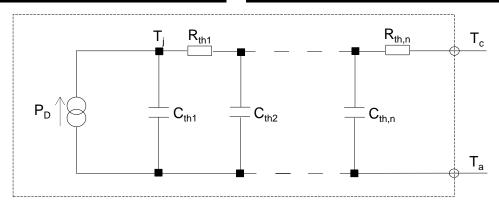
### ●Thermal resistance

Parameter	Symbol	Values			Unit
Falametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}^{^{*9}}$	-	0.43	0.56	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	4.1 ×10 <sup>-2</sup>	
R <sub>th2</sub>	1.8 ×10 <sup>-1</sup>	K/W
R <sub>th3</sub>	2.1 ×10 <sup>-1</sup>	

Symbol	Value	Unit
C <sub>th1</sub>	1.2 ×10 <sup>-3</sup>	
C <sub>th2</sub>	5.0 <b>×</b> 10 <sup>-3</sup>	Ws/K
C <sub>th3</sub>	4.7 ×10 <sup>-2</sup>	



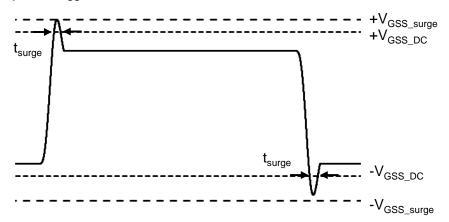
# ullet Electrical characteristics (T<sub>vj</sub> = 25°C unless otherwise specified)

Doromotor	Symbol	mbol Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g <sub>fs</sub> *8	$V_{DS} = 10V, I_{D} = 42A$	-	22	-	S
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	4532	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	129	-	pF
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	-	9	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 800V$	-	156	1	pF
Total Gate charge	Q <sub>g</sub> *8	$V_{DS} = 800V$ $I_{D} = 42A$	ı	170	ı	
Gate - Source charge	Q <sub>gs</sub> *8	$V_{GS} = 18V$	-	32	-	nC
Gate - Drain charge	Q <sub>gd</sub> *8	See Fig. 1-1, 1-2.	-	52	ı	
Turn - on delay time	t <sub>d(on)</sub> *8	$V_{DS} = 800V$ $I_{D} = 42A$	-	13	ı	
Rise time	t <sub>r</sub> *8	$V_{GS} = +18V / 0V$	-	21	ı	ns
Turn - off delay time	t <sub>d(off)</sub> *8	$R_G = 3.3\Omega$ , L = 250µH $E_{on}$ includes diode	-	50	-	115
Fall time	t <sub>f</sub> *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	11	-	
Turn - on switching loss	E <sub>on</sub> *8	See Fig. 2-1, 2-2, 2-3.	-	520	-	1
Turn - off switching loss	E <sub>off</sub> *8		-	142	1	μJ

# ●Body diode electrical characteristics (Source-Drain) (T<sub>vi</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			l lmi4
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V <sub>SD</sub> *8	$V_{GS} = 0V, I_{S} = 42A$	ı	3.3	-	V
Reverse recovery time	t <sub>rr</sub> *8	$I_F = 42A$ $V_R = 800V$	ı	12	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *8	di/dt = 4700A/µs	ı	252	ı	nC
Peak reverse recovery current	I <sub>rrm</sub> *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	44	-	Α

- \*1 Limited by maximum T<sub>vj</sub> and for Max. R<sub>thJC</sub>.
- \*2 Pulse width and duty cycle are limited by  $T_{v_j,max}$ .
- \*3 Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%
- \*4 When used as a protective function, PW ≤ 10µs
- \*5 Example of acceptable V<sub>GS</sub> waveform



Please note especially when using driver source that  $V_{\text{GSS\_surge}}$  must be in the range of absolute maximum rating.

- \*6 Please be advised not to use SiC-MOSFETs with V<sub>GS</sub> below 10V as doing so may cause thermal runaway.
- \*7 Tested after applying  $V_{GS} = 21V$  for 100ms.
- \*8 Pulsed
- \*9 Measured conformable to JESD51-14.

See the application note "rthjc\_measurement\_and\_usage\_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc\_measurement\_and\_usage\_an-e.pdf

Fig.1 Power Dissipation Derating Curve

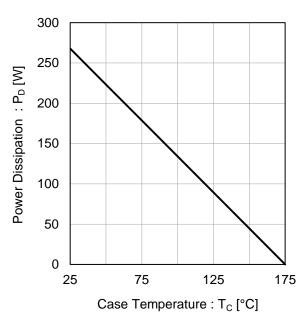


Fig.2 Maximum Safe Operating Area

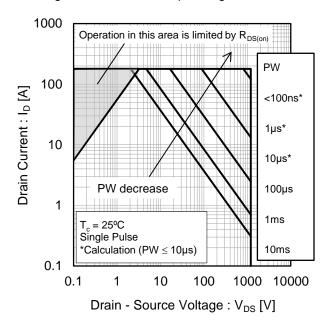
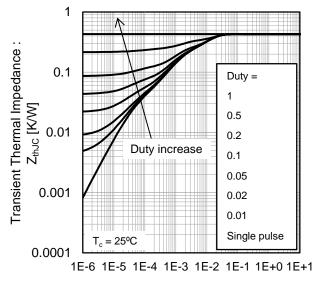
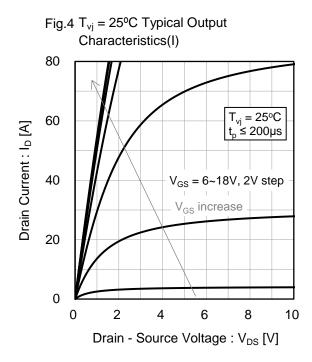


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



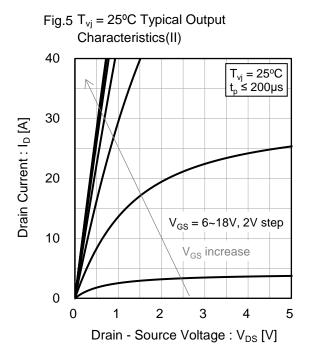
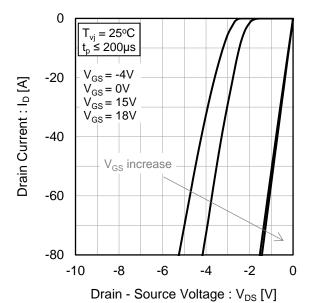
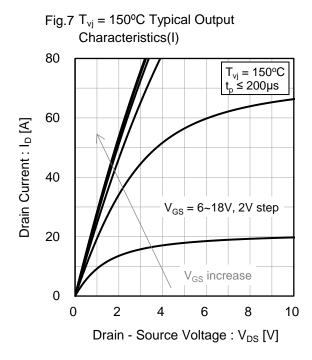
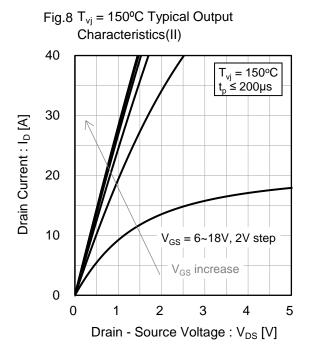
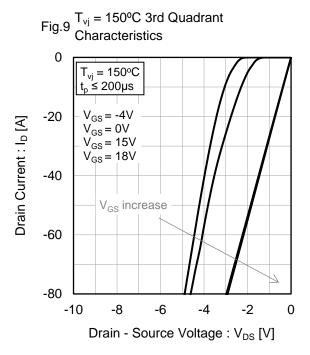


Fig.6  $T_{vj}$  = 25°C 3rd Quadrant Characteristics









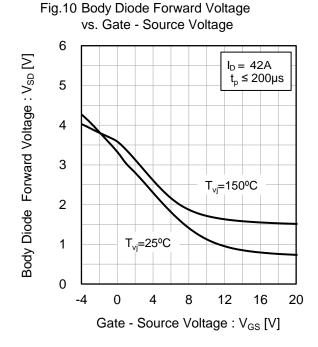


Fig.11 Typical Transfer Characteristics (I)

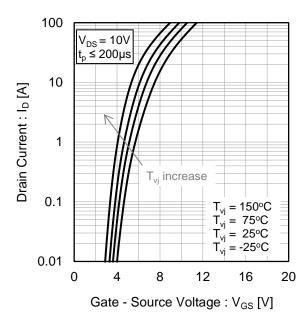


Fig.12 Typical Transfer Characteristics (II)

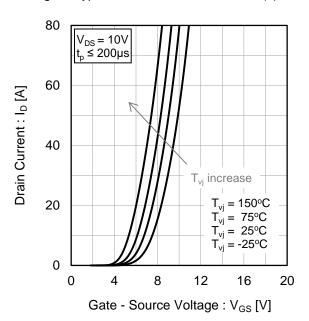


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

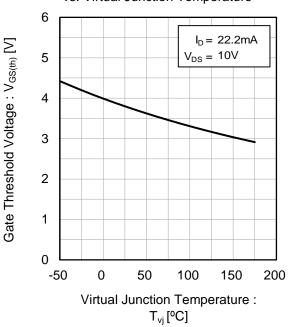


Fig.14 Transconductance vs. Drain Current

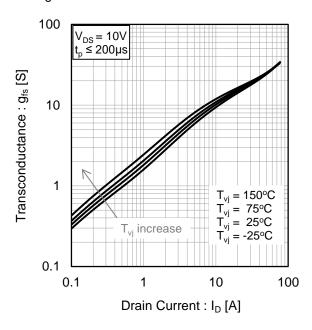


Fig.15 Static Drain - Source On - State
Resistance vs. Gate - Source Voltage

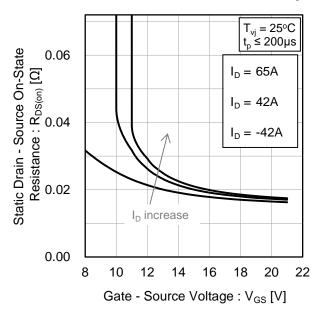


Fig.16 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

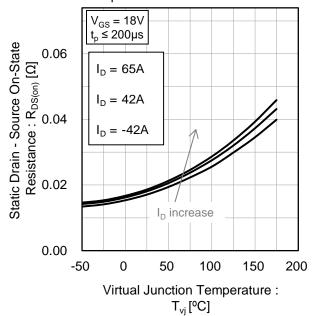


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

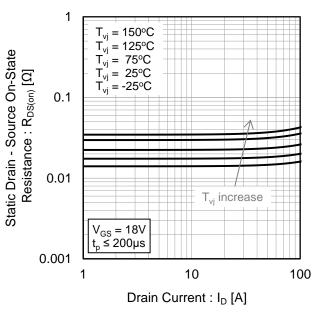
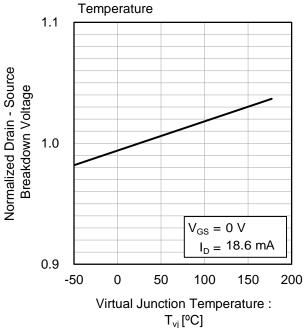
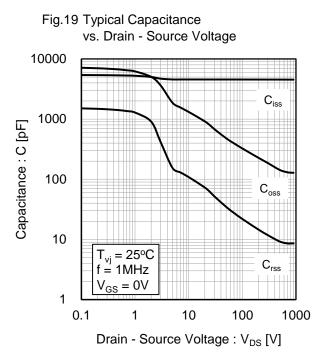


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Virtual Junction





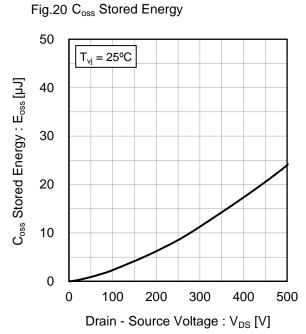
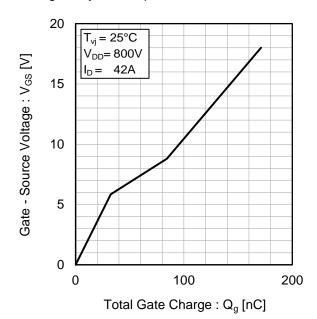


Fig.21 Dynamic Input Characteristics



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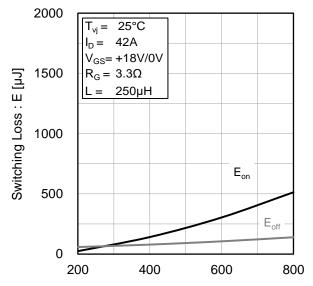
#### •Electrical characteristic curves

Fig.22 Typical Switching Time

vs. External Gate Resistance

250  $T_{vj} = 25^{\circ}C$   $I_{D} = 42A$   $V_{DD} = 800V$   $V_{GS} = +18V/0V$   $L = 250\mu H$  100 50  $t_{d(on)}$   $t_{d(on)}$ 

Fig.23 Typical Switching Loss vs. Drain - Source Voltage



External Gate Resistance :  $R_G[\Omega]$ 

10

15

20

Drain - Source Voltage :  $V_{DS}$  [V]

Fig.24 Typical Switching Loss vs. Drain Current

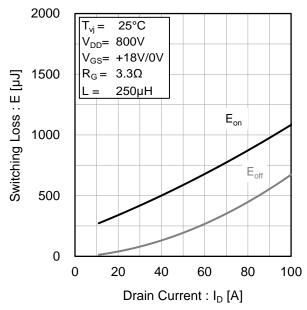
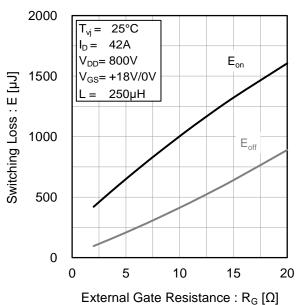


Fig.25 Typical Switching Loss vs. External Gate Resistance



#### • Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

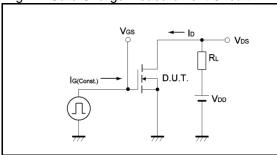


Fig.2-1 Switching Characteristics Measurement Circuit

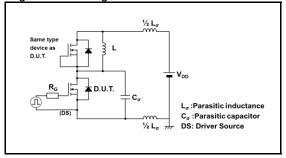


Fig.2-3 Waveforms for Switching Energy Loss

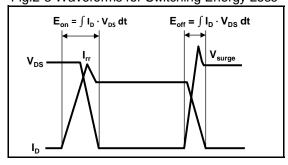


Fig.3-1 Reverse Recovery Time Measurement Circuit

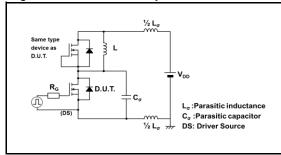


Fig.1-2 Gate Charge Waveform

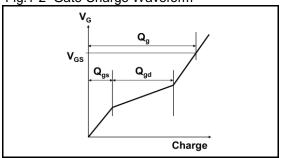


Fig.2-2 Waveforms for Switching Time

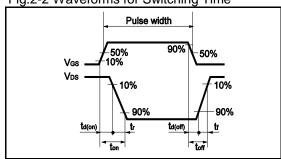
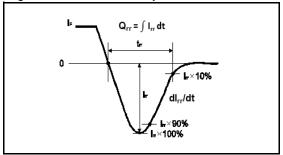
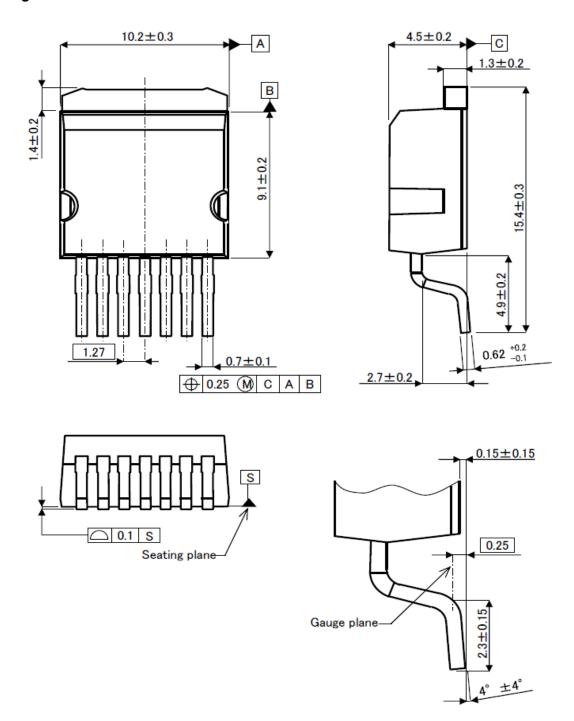


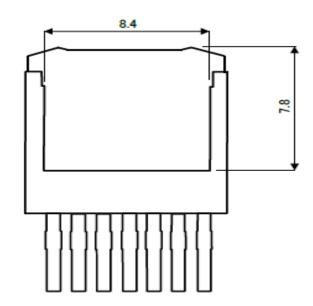
Fig.3-2 Reverse Recovery Waveform



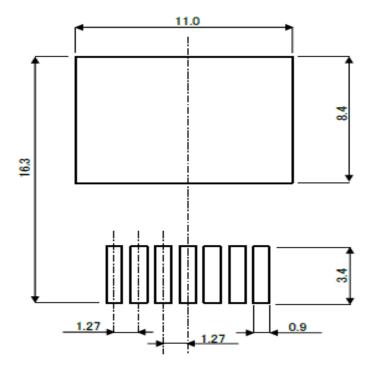
## ●Package Dimensions



Unit: mm

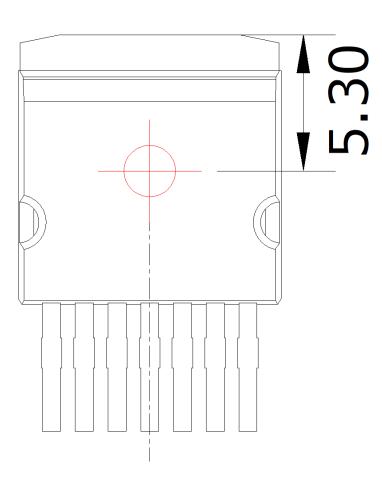


# RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

## **●**Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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